

AMENDMENT TRANSMITTAL LETTER					Docket No. V0195.0008	
Application No. 10/768,971-Conf. #4544	Filing Date January 30, 2004	Examiner E. J. Wojciechowicz	Art Unit 2815			
Applicant(s): Franz Hofmann et al.						
Invention: Fin field-effect transistor and method for producing a fin field effect-transistor						
TO THE COMMISSIONER FOR PATENTS						
Transmitted herewith is an amendment in the above-identified application.						
The fee has been calculated and is transmitted as shown below.						
CLAIMS AS AMENDED						
	Claims Remaining After Amendment	Highest Number Previously Paid	Number Extra Claims Present	Rate		
Total Claims	17	- 27 =	0	x 50.00	0.00	
Independent Claims	2	- 3 =	0	x 200.00	0.00	
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>						
Other fee (please specify):						
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT:					0.00	
<input checked="" type="checkbox"/> Large Entity <input type="checkbox"/> Small Entity						
<input checked="" type="checkbox"/> No additional fee is required for this amendment.						
<input type="checkbox"/> Please charge Deposit Account No. _____ in the amount of \$ _____. A duplicate copy of this sheet is enclosed.						
<input type="checkbox"/> A check in the amount of \$ _____ to cover the filing fee is enclosed.						
<input type="checkbox"/> Payment by credit card.						
<input checked="" type="checkbox"/> The Director is hereby authorized to charge and credit Deposit Account No. <u>50-2215</u> as described below. A duplicate copy of this sheet is enclosed.						
<input checked="" type="checkbox"/> Credit any overpayment.						
<input checked="" type="checkbox"/> Charge any additional filing or application processing fees required under 37 CFR 1.16 and 1.17.						
<i>Laura C. Brutman</i> Laura C. Brutman Attorney/Agent Reg. No.: 38,395					Dated: <u>March 19, 2007</u>	
DICKSTEIN SHAPIRO LLP 1177 Avenue of the Americas 41st Floor New York, New York 10036-2714 (212) 277-6592						

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Franz Hofmann et al.

Application No.: 10/768,971

Confirmation No.: 4544

Filed: January 30, 2004

Art Unit: 2815

For: Fin field-effect transistor and method for
producing a fin field effect-transistor

Examiner: E. J. Wojciechowicz

AMENDMENT AFTER FINAL ACTION UNDER 37 C.F.R. 1.116

MS AF
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

INTRODUCTORY COMMENTS

In response to the Advisory Action dated October 2, 2006, and in further response to the Office Action dated March 23, 2006, the following Remarks are respectfully submitted.

Claims are reflected in the listing of claims which begins on page 2 of this paper.

Remarks/Arguments begin on page 6 of this paper.